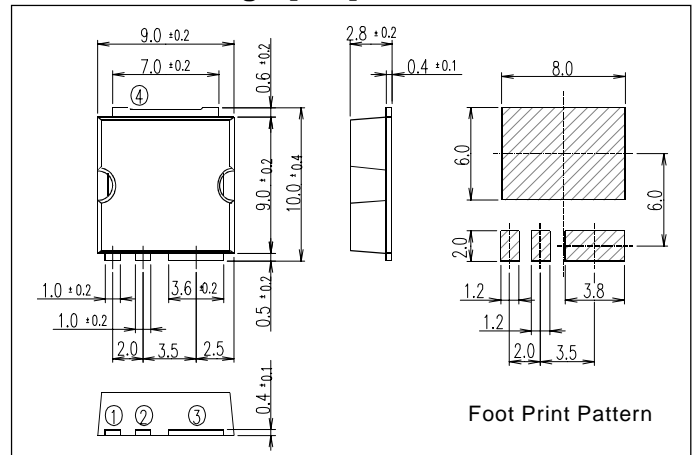


Super FAP-G Series

N-CHANNEL SILICON POWER MOSFET

■ Outline Drawings [mm]



■ Features

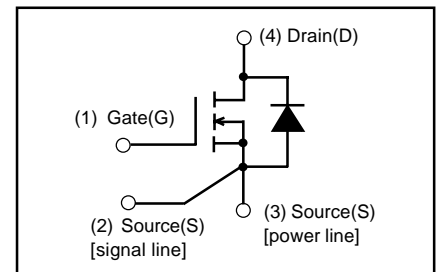
- High speed switching
- Low on-resistance
- No secondary breakdown
- Low driving power
- Avalanche-proof

■ Applications for Switching

■ Absolute Maximum Ratings at $T_c=25^\circ\text{C}$ (unless otherwise specified)

Item	Symbol	Ratings	Unit	Remarks
Drain-source voltage	V_{DS}	250	V	
	V_{DSX}	220	V	$V_{GS}=30\text{V}$
Continuous drain current	I_D	± 37	A	
		± 3.4 *4	A	$T_a=25^\circ\text{C}$
Pulsed drain current	$I_{D(puls)}$	± 148	A	
Gate-source voltage	V_{GS}	± 30	V	
Repetitive or non-repetitive	I_{AR} *2	37	A	
Maximum Avalanche Energy	E_{AS} *1	251.9	mJ	
Maximum Drain-Source dV/dt	dV_{DS}/dt	20	kV/ μs	$V_{DS} \leq 250\text{V}$
Peak Diode Recovery dV/dt	dV/dt *3	5	kV/ μs	
Max. power dissipation	P_D	2.4 *4	W	$T_a=25^\circ\text{C}$
		270	W	
Operating and storage temperature range	T_{ch}	+150	$^\circ\text{C}$	
	T_{stg}	-55 to +150	$^\circ\text{C}$	

■ Equivalent circuit schematic



*1 $L=0.309\text{mH}$, $V_{CC}=48\text{V}$, See to Avalanche Energy Graph *2 $T_{ch} \leq 150^\circ\text{C}$ *3 $I_F \leq -I_D$, $-di/dt=50\text{A}/\mu\text{s}$, $V_{CC} \leq BV_{DS}$, $T_{ch} \leq 150^\circ\text{C}$

*4 Surface mounted on 1000mm^2 , $t=1.6\text{mm}$ FR-4 PCB(Drain pad area: 500mm^2)

● Electrical characteristics at $T_c=25^\circ\text{C}$ (unless otherwise specified)

Item	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Drain-source breakdown voltage	$V_{(BR)DSS}$	$I_D=250\mu\text{A}$ $V_{GS}=0\text{V}$	250			V
Gate threshold voltage	$V_{GS(th)}$	$I_D=250\mu\text{A}$ $V_{DS}=V_{GS}$	3.0		5.0	V
Zero gate voltage drain current	I_{DSS}	$V_{DS}=250\text{V}$ $V_{GS}=0\text{V}$			25	μA
		$V_{DS}=200\text{V}$ $V_{GS}=0\text{V}$			250	
Gate-source leakage current	I_{GSS}	$V_{GS}=\pm 30\text{V}$ $V_{DS}=0\text{V}$		10	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	$I_D=12.5\text{A}$ $V_{GS}=10\text{V}$		75	100	$\text{m}\Omega$
Forward transconductance	g_{fs}	$I_D=12.5\text{A}$ $V_{DS}=25\text{V}$	8	16		S
Input capacitance	C_{iss}	$V_{DS}=75\text{V}$		2000	3000	pF
Output capacitance	C_{oss}	$V_{GS}=0\text{V}$		220	330	
Reverse transfer capacitance	C_{rss}	$f=1\text{MHz}$		15	30	
Turn-on time t_{on}	$t_{d(on)}$	$V_{CC}=72\text{V}$ $I_D=12.5\text{A}$		20	30	ns
	t_r	$V_{GS}=10\text{V}$		30	45	
Turn-off time t_{off}	$t_{d(off)}$	$R_{GS}=10\Omega$		60	90	
	t_f			20	30	
Total Gate Charge	Q_G	$V_{CC}=72\text{V}$		44	66	nC
Gate-Source Charge	Q_{GS}	$I_D=25\text{A}$		14	21	
Gate-Drain Charge	Q_{GD}	$V_{GS}=10\text{V}$		16	24	
Avalanche capability	I_{AV}	$L=309\mu\text{H}$ $T_{ch}=25^\circ\text{C}$	37			A
Diode forward on-voltage	V_{SD}	$I_F=25\text{A}$ $V_{GS}=0\text{V}$ $T_{ch}=25^\circ\text{C}$		1.10	1.65	V
Reverse recovery time	t_{rr}	$I_F=25\text{A}$ $V_{GS}=0\text{V}$		0.45		μs
Reverse recovery charge	Q_{rr}	$-di/dt=100\text{A}/\mu\text{s}$ $T_{ch}=25^\circ\text{C}$		1.5		μC

● Thermal characteristics

Item	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Thermal resistance	$R_{th(ch-c)}$	channel to case			0.463	$^\circ\text{C}/\text{W}$
	$R_{th(ch-a)}$	channel to ambient			87.0	$^\circ\text{C}/\text{W}$
	$R_{th(ch-a)}$ *4	channel to ambient			52.0	$^\circ\text{C}/\text{W}$

Characteristics

